## NSN 5961-01-031-8485

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View Online at https://aerobasegroup.com/nsn/5961-01-031-8485 **Inclosure Material:** Metal **Overall Length:** 1.573 inches **Overall Height:** 0.450 inches **Overall Width:** 1.050 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: **Electrode Internally-electrically Connected To Case: Internal Junction Configuration:** Pnp **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 60.0 breakdown voltage, collector-to-base, emitter open and 7.0 emitter to base voltage, static, collector open and 60.0 breakdown voltage, collector-to-emitter, base open **Current Rating Per Characteristic:** 10.00 amperes source cutoff current and 4.00 amperes source cutoff current **Power Rating Per Characteristic:** 150.0 watts small-signal input power, common-collector **Transfer Ratio:** 90.0 static forward current transfer ratio, common-emitter **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Terminal Type And Quantity:** 2 pin and 1 case Shelf Life: N/a

No

**Unit Of Measure:** 

Demilitarization:

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